

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Application Number	10/719,663
	Filing Date	November 20, 2003
	First Named Inventor	Faris
	Group Art Unit	2818
	Examiner Name	Nguyen, Dao H
Sheet 1 of 6	Attorney Docket Number	Reveo-0202USAAON00

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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOC. NO.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
DN		4,309,225	05-Jan-82	Fan et al.	148	1.5	
		4,370,176	25-Jan-83	Bruel	148	1.5	
		4,371,421	01-Feb-83	Fan et al.	166	624	
		4,471,003	11-Sep-84	Cann	427	34	
		4,479,846	30-Oct-84	Smith et al.	156	603	
		4,500,563	19-Feb-85	Eilenberger et al.	427	38	
		4,585,945	29-Apr-86	Bruel et al.	250	492.2	
		4,816,420	28-Mar-89	Bozler et al.	437	2	
		4,837,182	06-Jun-89	Bozler et al.	437	82	
		4,846,931	11-Jul-89	Gmitter et al.	156	633	
		4,883,561	28-Nov-89	Gmitter et al.	156	633	
		5,273,616	28-Dec-93	Bozler et al.	156	603	
		5,362,682	08-Nov-94	Bozler et al.	437	226	
		5,374,564	20-Dec-94	Bruel	437	24	
		5,453,153	26-Sep-95	Fan et al.	117	2	
		5,559,043	24-Sep-96	Bruel	437	424	
		5,588,994	31-Dec-96	Bozler et al.	117	89	
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		5,710,057	20-Jan-98	Kenney	437	62	
		5,714,395	03-Feb-98	Bruel	437	24	
		5,793,115	11-Aug-98	Zavracky et al.	257	777	
		5,845,123	01-Dec-98	Johnson et al.	395	377	
		5,877,070	02-Mar-99	Goesele et al.	438	458	
		5,882,987	16-Mar-99	Srikrishnan	438	458	
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		5,920,764	06-Jul-99	Hanson et al.	438	4	
		5,933,750	03-Aug-99	Wilson et al.	438	455	
		5,976,953	02-Nov-99	Zavracky et al.	438	455	
		5,985,688	16-Nov-99	Bruel	438	53	
		5,993,677	30-Nov-99	Biasse et al.	216	36	
		5,994,207	30-Nov-99	Henley et al.	438	515	
		6,020,252	01-Feb-00	Aspar et al.	438	458	
		6,027,988	22-Feb-00	Cheung et al.	483	513	
		6,033,974	07-Mar-00	Henley et al.	438	526	
		6,054,363	25-Apr-00	Sakaguchi et al.	438	406	
		6,054,370	25-Apr-00	Doyle	438	456	
		6,059,877	09-May-00	Bruel	117	35	
		6,071,795	08-Jun-00	Cheung et al.	438	458	
		6,103,597	15-Aug-00	Aspar et al.	438	458	
DN		6,137,110	24-Oct-00	Pellin et al.	250	423	

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FOREIGN PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
DN	EP0355913A1	28-Feb-90	Europe				
	WO 95/20824A1	3-Aug-95	PCT				
	WO 98/20543A2	14-May-98	PCT				
	WO 98/33209	30-Jul-98	PCT				
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	WO 00/48238A1	17-Aug-00	PCT				
	EP01045448A1	18-Oct-00	Europe				
	WO 00/75995A1	14-Dec-00	PCT				
	WO 00/75968A1	14-Dec-00	PCT				
	WO 01/03172A1	11-Jan-01	PCT				
	WO 01/03171A1	11-Jan-01	PCT				
	JP 63-155731	Jun 1988	JP				X
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